

# Quad Switching Transistor

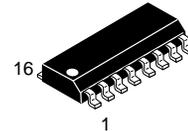
## NPN Silicon

### MAXIMUM RATINGS

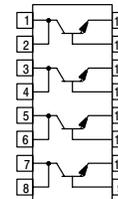
| Rating   | Symbol         | Value                  |                                     | Unit                          |
|--|----------------|------------------------|-------------------------------------|-------------------------------|
| Collector–Emitter Voltage  | $V_{CEO}$      | 15                     |                                     | Vdc                           |
| Collector–Base Voltage   | $V_{CB}$       | 40                     |                                     | Vdc                           |
| Emitter–Base Voltage   | $V_{EB}$       | 4.5                    |                                     | Vdc                           |
| Collector Current — Continuous   | $I_C$          | 500                    |                                     | mAdc                          |
|  |                | <b>Each Transistor</b> | <b>Four Transistors Equal Power</b> |                               |
| Total Power Dissipation<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 0.4<br>3.2             | 0.72<br>6.4                         | Watts<br>mW/ $^\circ\text{C}$ |
| Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 0.66<br>5.3            | 1.92<br>15.4                        | Watts<br>mW/ $^\circ\text{C}$ |
| Operating and Storage<br>Junction Temperature Range                                      | $T_J, T_{stg}$ | –55 to +150            |                                     | $^\circ\text{C}$              |

# MMPQ2369

ON Semiconductor Preferred Device



CASE 751B–05, STYLE 4  
SO–16



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|   |               |     |   |     |                 |
|---|---------------|-----|---|-----|-----------------|
| Collector–Emitter Breakdown Voltage <sup>(1)</sup><br>( $I_C = 10\text{ mAdc}, I_E = 0$ ) | $V_{(BR)CEO}$ | 15  | — | —   | Vdc             |
| Collector–Base Breakdown Voltage<br>( $I_C = 10\ \mu\text{Adc}, I_E = 0$ )                | $V_{(BR)CBO}$ | 40  | — | —   | Vdc             |
| Emitter–Base Breakdown Voltage<br>( $I_E = 10\ \mu\text{Adc}, I_C = 0$ )                  | $V_{(BR)EBO}$ | 4.5 | — | —   | Vdc             |
| Collector Cutoff Current<br>( $V_{CB} = 20\text{ Vdc}, I_E = 0$ )                         | $I_{CBO}$     | —   | — | 0.4 | $\mu\text{Adc}$ |

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MMPQ2369

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

| Characteristic  | Symbol        | Min      | Typ    | Max    | Unit |
|---|---------------|----------|--------|--------|------|
| <b>ON CHARACTERISTICS</b>   |               |          |        |        |      |
| DC Current Gain <sup>(1)</sup><br>( $I_C = 10\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )<br>( $I_C = 100\text{ mA}$ , $V_{CE} = 2.0\text{ Vdc}$ ) | $h_{FE}$      | 40<br>20 | —<br>— | —<br>— | —    |
| Collector–Emitter Saturation Voltage<br>( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ )  | $V_{CE(sat)}$ | —        | —      | 0.25   | Vdc  |
| Base–Emitter Saturation Voltage<br>( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ )   | $V_{BE(sat)}$ | —        | —      | 0.9    | Vdc  |
| <b>DYNAMIC CHARACTERISTICS</b>  |               |          |        |        |      |
| Current–Gain — Bandwidth Product<br>( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 100\text{ MHz}$ )                                  | $f_T$         | 450      | 550    | —      | MHz  |
| Output Capacitance<br>( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )  | $C_{ob}$      | —        | 2.5    | 4.0    | pF   |
| Input Capacitance<br>( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )   | $C_{ib}$      | —        | 3.0    | 5.0    | pF   |
| <b>SWITCHING CHARACTERISTICS</b>  |               |          |        |        |      |
| Turn–On Time<br>( $V_{CC} = 3.0\text{ Vdc}$ , $V_{EB(off)} = 1.5\text{ Vdc}$ , $I_C = 10\text{ mA}$ ,<br>$I_{B1} = 3.0\text{ mA}$ )             | $t_{on}$      | —        | 9.0    | —      | ns   |
| Turn–Off Time<br>( $V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 3.0\text{ mA}$ , $I_{B2} = 1.5\text{ mA}$ )                     | $t_{off}$     | —        | 15     | —      | ns   |

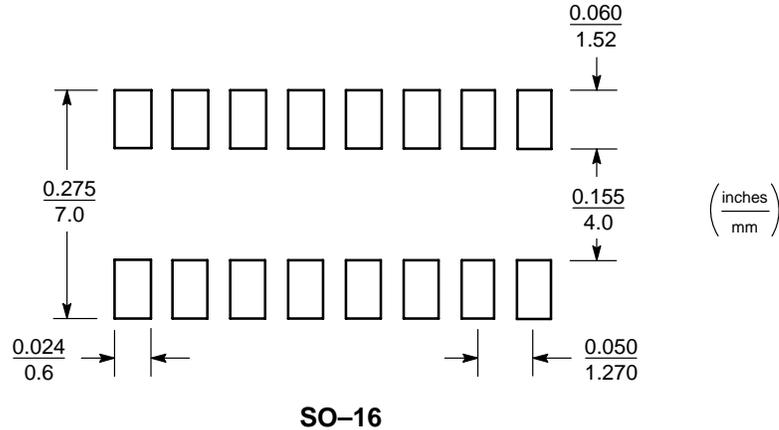
1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .

## INFORMATION FOR USING THE SO-16 SURFACE MOUNT PACKAGE

### MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



### SO-16 POWER DISSIPATION

The power dissipation of the SO-16 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient, and the operating temperature,  $T_A$ . Using the values provided on the data sheet for the SO-16 package,  $P_D$  can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 1.0 watt.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{125^\circ\text{C/W}} = 1.0 \text{ watt}$$

The 125°C/W for the SO-16 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 1.0 watt. There are other alternatives to achieving higher power dissipation from the SO-16 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

### SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

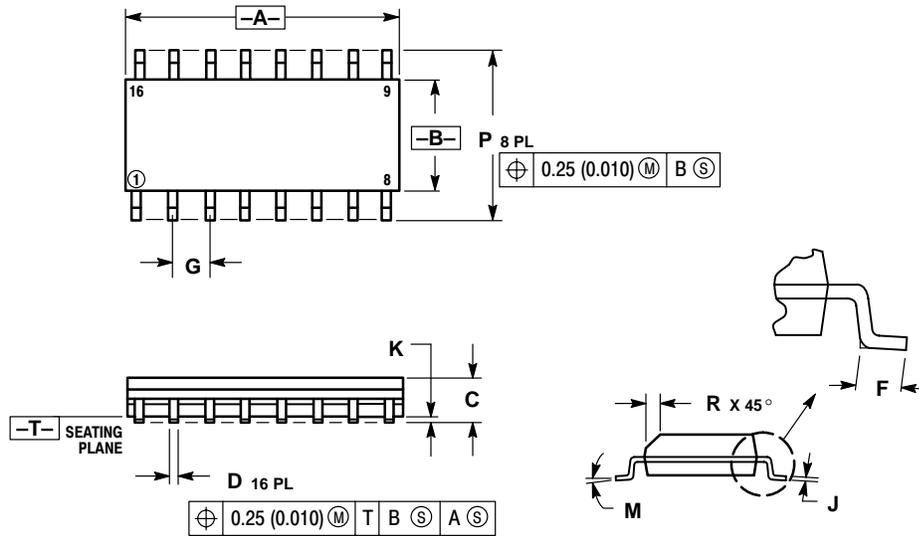
- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

# MMPQ2369

## PACKAGE DIMENSIONS

### CASE 751B-05 SO-16 ISSUE J



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| DIM | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
|     | MIN         | MAX   | MIN       | MAX   |
| A   | 9.80        | 10.00 | 0.386     | 0.393 |
| B   | 3.80        | 4.00  | 0.150     | 0.157 |
| C   | 1.35        | 1.75  | 0.054     | 0.068 |
| D   | 0.35        | 0.49  | 0.014     | 0.019 |
| F   | 0.40        | 1.25  | 0.016     | 0.049 |
| G   | 1.27 BSC    |       | 0.050 BSC |       |
| J   | 0.19        | 0.25  | 0.008     | 0.009 |
| K   | 0.10        | 0.25  | 0.004     | 0.009 |
| M   | 0°          | 7°    | 0°        | 7°    |
| P   | 5.80        | 6.20  | 0.229     | 0.244 |
| R   | 0.25        | 0.50  | 0.010     | 0.019 |

#### STYLE 4:

- PIN 1:
- COLLECTOR, DYE #1
  - COLLECTOR, #1
  - COLLECTOR, #2
  - COLLECTOR, #2
  - COLLECTOR, #3
  - COLLECTOR, #3
  - COLLECTOR, #4
  - COLLECTOR, #4
  - BASE, #4
  - EMITTER, #4
  - BASE, #3
  - EMITTER, #3
  - BASE, #2
  - EMITTER, #2
  - BASE, #1
  - EMITTER, #1

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